# 100mW High Power Laser Diode

#### Description

The SLD301V is a gain-guided, high-power laser diode fabricated by MOCVD.

MOCVD: Metal Organic Chemical Vapor Deposition

#### **Features**

- High power
  - Recommended power output Po = 90mW
- Low operating current

#### **Applications**

- Solid state laser excitation
- Medical use

#### Structure

GaAlAs double-hetero-type laser diode

# 1. LD cathode 2. PD anode 3. COMMON **Bottom View**

**Pin Configuration** 

**Operating Lifetime** 

MTTF 10,000H (effective value) at Po = 90mW, Tc = 25°C

# Absolute Maximum Ratings (Tc = 25°C)

<ul> <li>Optical power output</li> </ul>	Po	100	mW
<ul> <li>Reverse voltage</li> </ul>	Vr LD	2	V
	PD	15	V
<ul> <li>Operating temperature</li> </ul>	Topr	-10 to +50	°C
<ul> <li>Storage temperature</li> </ul>	Tstg	-40 to +85	°C

#### Warranty

This warranty period shall be 90 days after receipt of the product or 1,000 hours operation time whichever is shorter.

Sony Quality Assurance Department shall analyze any product that fails during said warranty period, and if the analysis results show that the product failed due to material or manufacturing defects on the part of Sony, the product shall be replaced free of charge.

Laser diodes naturally have differing lifetimes which follow a Weibull distribution.

Special warranties are also available.

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#### **Electrical and Optical Characteristics**

(Tc: Case temperature,  $Tc = 25^{\circ}C$ )

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Item		Symbol	Conditions	Min.	Тур.	Max.	Unit
Threshold current		Ith			150	200	mA
Operating current		lop	Po = 90mW		250	400	mA
Operating voltage		Vop	Po = 90mW		1.9	3.0	V
Wavelength*1		λρ	Po = 90mW	770		840	nm
Monitor current		Imon	Po = 90mW VR = 10V		0.15		mA
Radiation angle (F. W. H. M.*)	Perpendicular	θΤ	Po = 90mW		28	40	degree
	Parallel	θ//			12	17	degree
Positional accuracy	Position	ΔΧ, ΔΥ	Po = 90mW			±50	μm
	Angle	Δφ⊥				±3	degree
Differential efficiency		ηο	Po = 90mW	0.65	0.9		mW/mA

<sup>\*</sup> F. W. H. M.: Full Width at Half Maximum

#### \*1 Wavelength Selection Classification

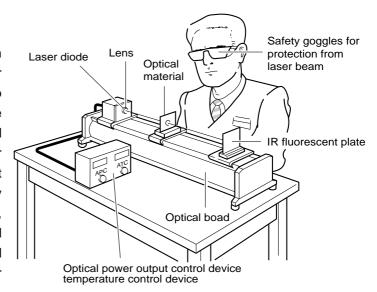
Туре	Wavelength (nm)
SLD301V-1	785 ± 15
SLD301V-2	810 ± 10
SLD301V-3	830 ± 10

Туре	Wavelength (nm)
SLD301V-21	798 ± 3
SLD301V-24	807 ± 3
SLD301V-25	810 ± 3

#### **Handling Precautions**

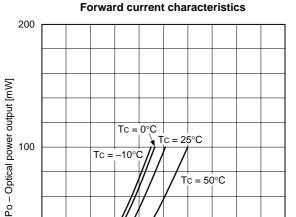
Eye protection against laser beams

The optical output of laser diodes ranges from several mW to 1W. However the optical power density of the laser beam at the diode chip reaches 1mW/cm². Unlike gas lasers, since laser diode beams are divergent, uncollinated laser diode beams are fairly safe at a laser diode. Generally speaking, however, it is best NOT to LOCK into laser beams, under any circumstances. For observing laser beams, ALWAYS use safety goggles that block infrared rays. Usage of IR scopes, IR cameras and fluorescent plates is also recommended for monitoring laser beams safely.



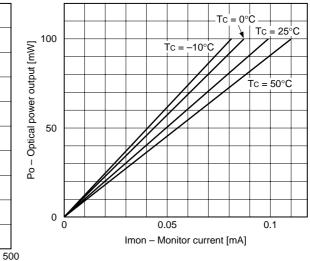
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#### **Example of Representative Characteristics**



Optical power output vs.

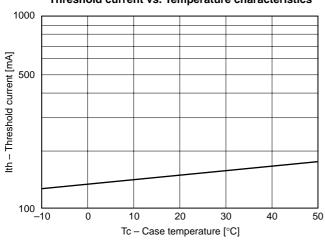
#### Optical power output vs. Monitor current characteristics



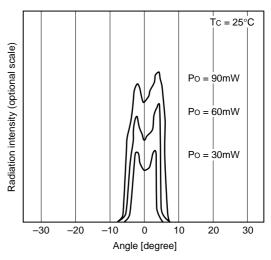
Threshold current vs. Temperature characteristics

250

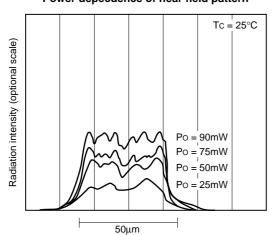
IF - Forward current [mA]



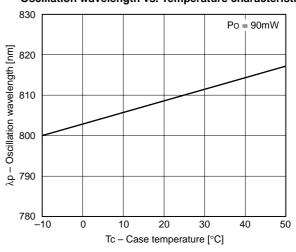
Power dependence of far field pattern (parallel to junction)



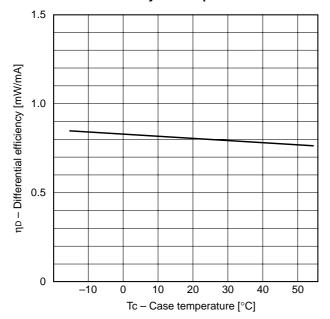
Power depecdence of near field pattern



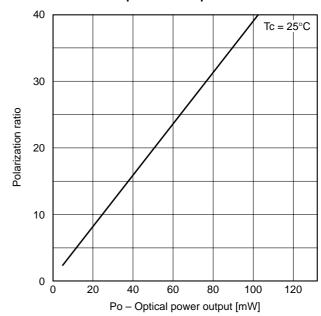
Oscillation wavelength vs. Temperature characteristics



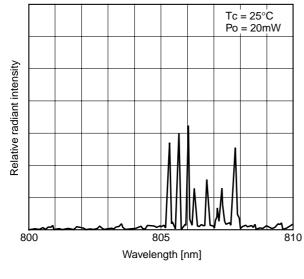
#### Differential efficiency vs. Temperature characteristics

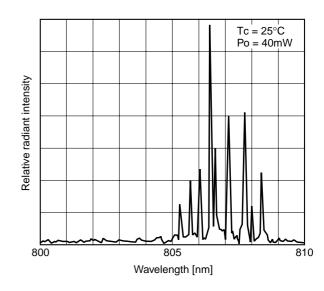


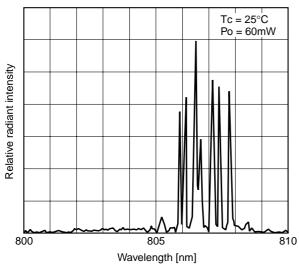
#### Power dependence of polarization ratio

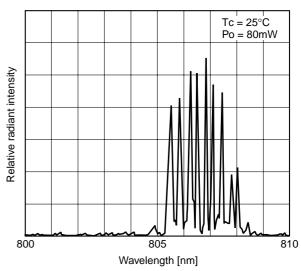


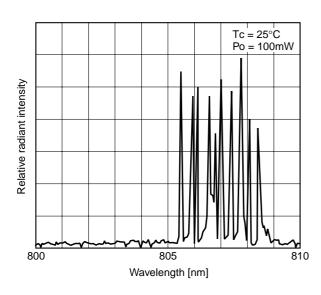
#### Power dependence of wavelength (Spectrum)



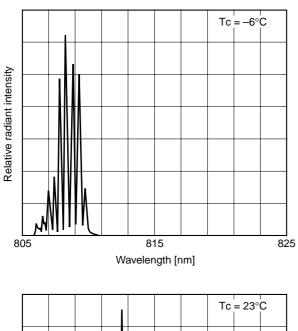


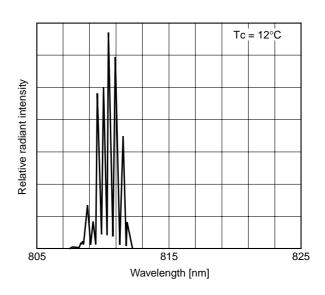


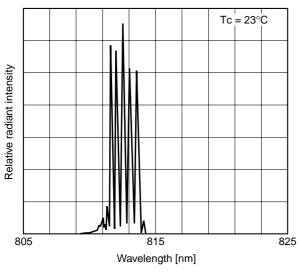


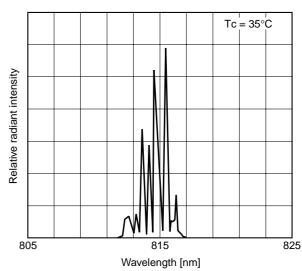


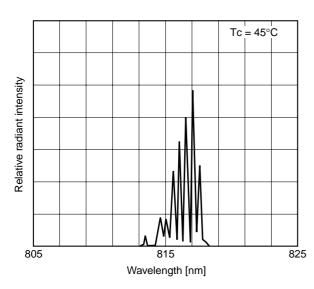
## Temperature dependence of wavelength (Po = 90mW)











### Package Outline Unit: mm

M-248 (LO-11)

